

FDS6680-NL-VB Datasheet

N-Channel 30-V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | | |
|---------------------|----------------------------------|---------------------------------|-----------------------|--|--|--|
| V _{DS} (V) | $R_{DS(on)}$ (Ω) | I _D (A) ^a | Q _g (Typ.) | | | |
| 30 | 0.008 at V _{GS} = 10 V | 13 | 6.1 nC | | | |
| 30 | 0.011 at V _{GS} = 4.5 V | 11 | 0.1110 | | | |

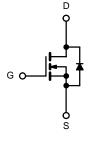
SO-8

FEATURES

- · Halogen-free
- TrenchFET® Power MOSFET
- Optimized for High-Side Synchronous Rectifier Operation
- 100 % R_g Tested
- 100 % UIS Tested

APPLICATIONS

- Notebook CPU Core
 - High-Side Switch



N-Channel MOSFET

| S | 1 | | 8 | D |
|---|---|----------|---|---|
| S | 2 | | 7 | D |
| S | 3 | | 6 | D |
| G | 4 | | 5 | D |
| | | | J | |
| | | Top View | | |
| | | | | |
| | | | | |

| ABSOLUTE MAXIMUM RATINGS | $T_A = 25$ °C, unles | s otherwise not | ed | | |
|---|------------------------|-----------------------------------|---------------------|----|--|
| Parameter | Symbol | Limit | Unit | | |
| Drain-Source Voltage | | V _{DS} | 30 | V | |
| Gate-Source Voltage | | V _{GS} | ± 20 | | |
| | T _C = 25 °C | | 13 | | |
| Continuous Drain Current (T _{.1} = 150 °C) | T _C = 70 °C | L_ | 10 | | |
| Continuous Diam Current (1) = 130 C) | T _A = 25 °C | I _D | 9 ^{b, c} | | |
| | T _A = 70 °C | | 7 ^{b, c} | A | |
| Pulsed Drain Current | | I _{DM} | 45 | A | |
| Continuous Source-Drain Diode Current | T _C = 25 °C | 1- | 3.7 | | |
| Continuous Source-Dialit Diode Current | T _A = 25 °C | I _S | 2.0 ^{b, c} | | |
| Single Pulse Avalanche Current | L = 0.1 mH | I _{AS} | 20 | | |
| Avalanche Energy | L = 0.111111 | E _{AS} | 21 | mJ | |
| | T _C = 25 °C | | 4.1 | | |
| Maximum Power Dissipation | T _C = 70 °C | P _D | 2.5 | W | |
| Maximum Power Dissipation | T _A = 25 °C | ' D | 2.2 ^{b, c} | VV | |
| | T _A = 70 °C | | 1.3 ^{b, c} | | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 150 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|---|--------------|-------------------|---------|---------|------|--|
| Parameter | | Symbol | Typical | Maximum | Unit | |
| Maximum Junction-to-Ambient ^{b, d} | t ≤ 10 s | R _{thJA} | 39 | 55 | °C/W | |
| Maximum Junction-to-Foot (Drain) | Steady State | R _{thJF} | 25 | 29 | C/VV | |

Notes:

- a. Base on $T_C = 25$ °C.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. Maximum under Steady State conditions is 85 °C/W.



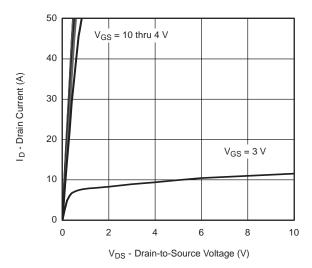
| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
|---|---------------------------|---|------|-------|-------|-------|--|
| Static | | , | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0 \text{ V, I}_{D} = 250 \mu\text{A}$ | 30 | | | V | |
| V _{DS} Temperature Coefficient | $\Delta V_{DS}/T_{J}$ | I _D = 250 μA | | 26 | | mV/°C | |
| V _{GS(th)} Temperature Coefficient | $\Delta V_{GS(th)}/T_{J}$ | I _D = 250 μA | | - 6 | | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$ | 1.0 | | 3.0 | V | |
| Gate-Source Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ± 100 | nA | |
| Zara Oata Valla va Busia Oamaat | | $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$ | | | 1 | μА | |
| Zero Gate Voltage Drain Current | IDSS | $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$ | | | 10 | | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$ | 20 | | | Α | |
| | _ | V _{GS} = 10 V, I _D = 10 A | | 0.008 | | | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = 4.5 V, I _D = 9 A | | 0.011 | | Ω | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = 15 V, I _D = 10 A | | 50 | | S | |
| Dynamic ^b | | | | | l | | |
| Input Capacitance | C _{iss} | | | 800 | | | |
| Output Capacitance | C _{oss} | V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz | | 165 | | pF | |
| Reverse Transfer Capacitance | C _{rss} | | | 73 | | | |
| Total Gate Charge | Qg | V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A | | 15 | 23 | nC | |
| | | | | 6.8 | 10.2 | | |
| Gate-Source Charge | Q _{gs} | $V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 10 \text{ A}$ | | 2.5 | | | |
| Gate-Drain Charge | Q_{gd} | | | 2.3 | | | |
| Gate Resistance | R_g | f = 1 MHz | 0.36 | 1.8 | 3.6 | Ω | |
| Turn-On Delay Time | t _{d(on)} | | | 16 | 23 | | |
| Rise Time | t _r | V_{DD} = 15 V, R_L = 1.4 Ω | | 12 | 16 | | |
| Turn-Off Delay Time | t _{d(off)} | $I_D \cong 9 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$ | | 16 | 22 | | |
| Fall Time | t _f | | | 10 | 18 |] | |
| Turn-On Delay Time | t _{d(on)} | | | 8 | 16 | ns | |
| Rise Time | t _r | V_{DD} = 15 V, R_L = 1.4 Ω | | 10 | 20 |] | |
| Turn-Off Delay Time | t _{d(off)} | $I_D \cong 9 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$ | | 16 | 22 | | |
| Fall Time | t _f | | | 8 | 15 | | |
| Drain-Source Body Diode Characterist | ics | | | | | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | | | 10 | ^ | |
| Pulse Diode Forward Current ^a | I _{SM} | | | | 50 | A | |
| Body Diode Voltage | V_{SD} | I _S = 9 A | | 0.8 | 1.2 | V | |
| Body Diode Reverse Recovery Time | t _{rr} | | | 15 | 30 | ns | |
| Body Diode Reverse Recovery Charge | Q _{rr} | I _F = 9 A, dI/dt = 100 A/μs, T _J = 25 °C | | 6 | 12 | nC | |
| Reverse Recovery Fall Time | t _a | i _F = θ A, αί/αι = 100 Α/μs, 1 _J = 25 °C | | 8 | | | |
| Reverse Recovery Rise Time | t _b | | | | | ns | |

Notes:

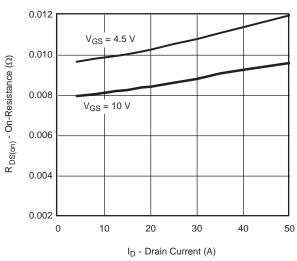
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

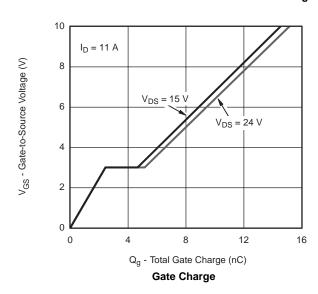




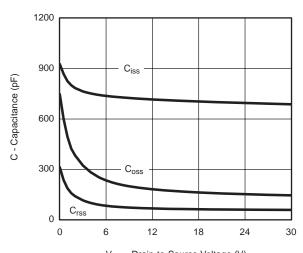
Output Characteristics



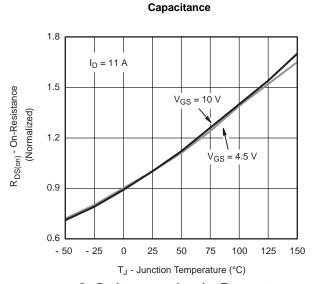
On-Resistance vs. Drain Current and Gate Voltage



V_{GS} - Gate-to-Source Voltage (V) **Transfer Characteristics**

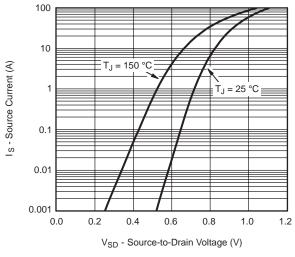


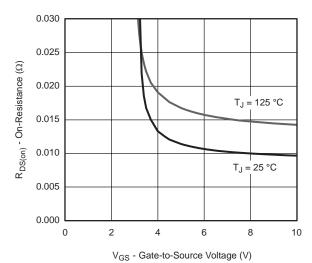
V_{DS} - Drain-to-Source Voltage (V)



On-Resistance vs. Junction Temperature

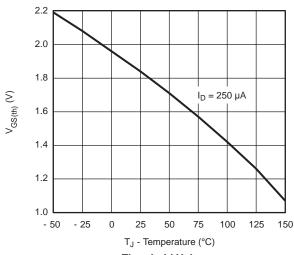


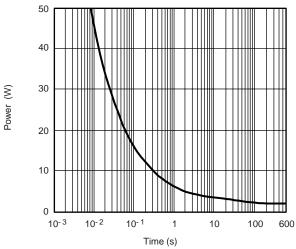




Source-Drain Diode Forward Voltage

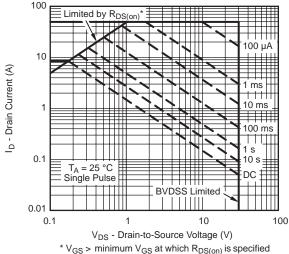






Threshold Voltage

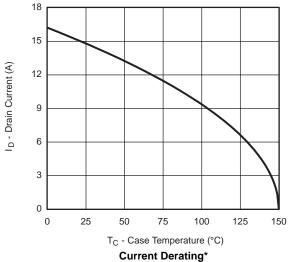
Single Pulse Power, Junction-to-Ambient



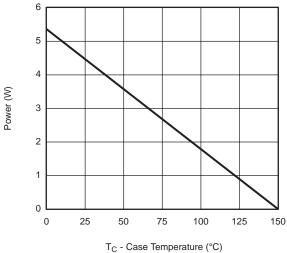
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

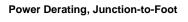
Safe Operating Area, Junction-to-Ambient

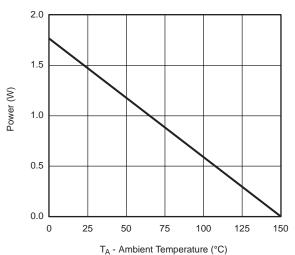








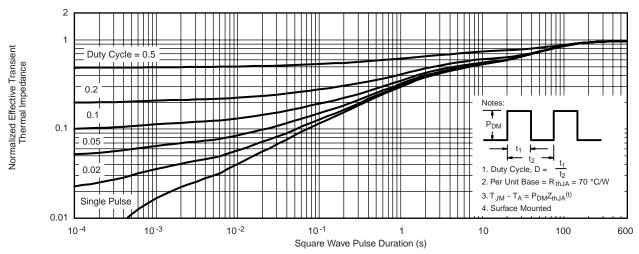




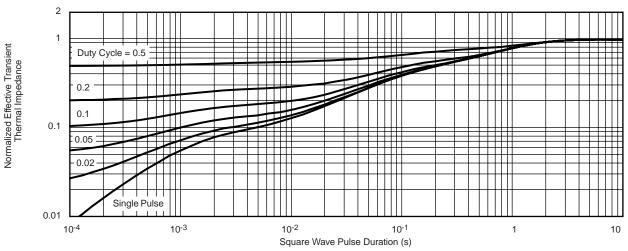
Power Derating, Junction-to-Ambient

^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





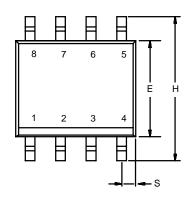
Normalized Thermal Transient Impedance, Junction-to-Ambient

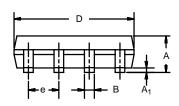


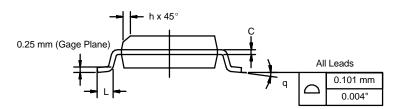
Normalized Thermal Transient Impedance, Junction-to-Foot



SOIC (NARROW): 8-LEAD







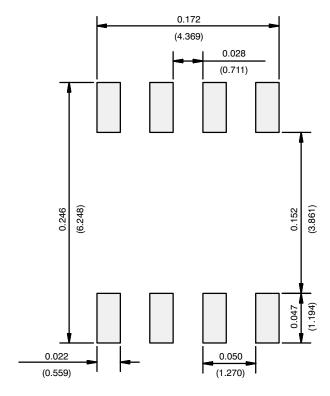
| | MILLIMETERS | | INC | HES | |
|--------------------------------|-------------|-----------------|--------|-------|--|
| DIM | Min | Max | Min | Max | |
| Α | 1.35 | 1.75 | 0.053 | 0.069 | |
| A ₁ | 0.10 | 0.20 | 0.004 | 0.008 | |
| В | 0.35 | 0.51 | 0.014 | 0.020 | |
| С | 0.19 | 0.25 | 0.0075 | 0.010 | |
| D | 4.80 | 5.00 | 0.189 | 0.196 | |
| E | 3.80 | 4.00 | 0.150 | 0.157 | |
| е | 1.27 | 7 BSC 0.050 BSC | | | |
| Н | 5.80 | 6.20 | 0.228 | 0.244 | |
| h | 0.25 | 0.50 | 0.010 | 0.020 | |
| L | 0.50 | 0.93 | 0.020 | 0.037 | |
| q | 0° | 8° | 0° | 8° | |
| S | 0.44 | 0.64 | 0.018 | 0.026 | |
| FCN: C-06527-Rev. I. 11-Sen-06 | | | | | |

ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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